



(19)

(11) Publication number: **2000**

Generated Document.

**PATENT ABSTRACTS OF JAPAN**(21) Application number: **11055684**(51) Intl. Cl.: **B24B 37/00 H01L 21/304**(22) Application date: **03.03.99**

(30) Priority:	(71) Applicant: <b>OKAMOTO MACHINE WORKS LTD</b>
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**(54) WAFER POLISHING PAD****(57) Abstract:**

**PROBLEM TO BE SOLVED:** To provide a CMP polishing pad which has a small difference in level between an insulation film and a metal layer, provides wafers excellent in uniformity, and is excellent in heat resistance.

**SOLUTION:** In a polishing pad which is used to polish wafers by pressing the polishing pad itself against the surface of a wafer to be polished and making the rotating polishing pad itself slide against the surface of the wafer which is rotated by rotating the spindle shaft of a wafer chucking mechanism and the spindle shaft of the polishing pad, a hard resin surface layer for sliding the wafer face of the polishing pad includes 0.5 to 10 wt.% of white solid lubricant selected from urea, melamine, isocyanuric acid and melamine.isocyanurate whose grain diameter is 0.1  $\mu\text{m}$  or less and boehmite abrasion grains.